

isc Silicon NPN Power Transistors

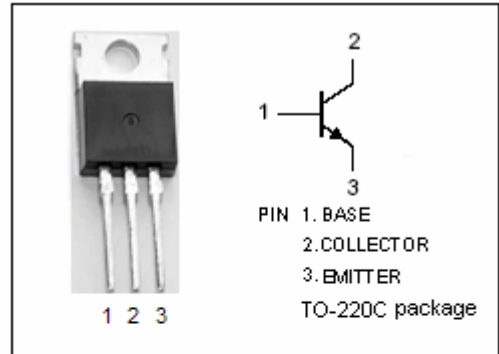
TIP29A

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 60V(\text{Min})$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = 0.7V(\text{Max.})@I_C = 1.0A$
- Complement to Type TIP30A

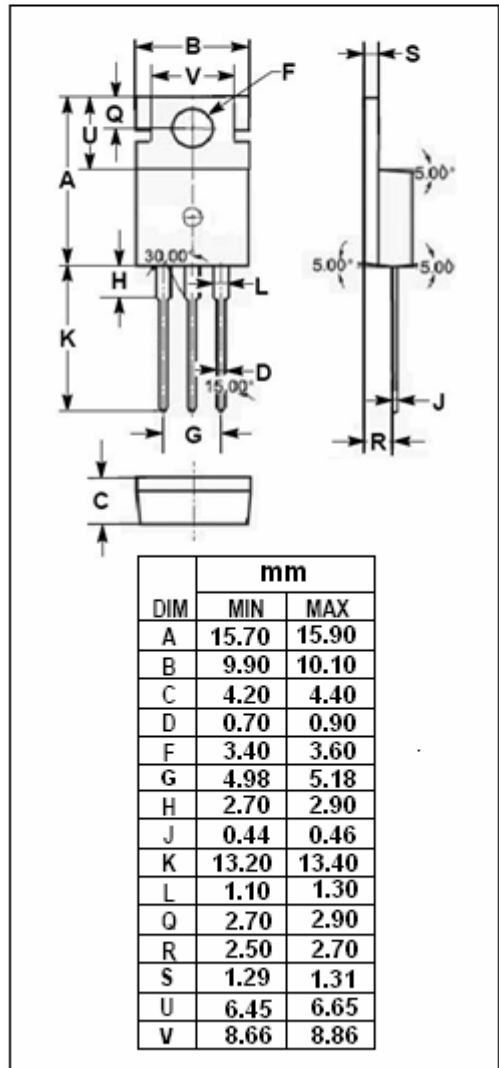
APPLICATIONS

- Designed for use in general purpose amplifier and switching applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	1	A
I_{CM}	Collector Current-Pulse	3	A
I_B	Base Current	0.4	A
P_C	Collector Power Dissipation $T_C=25^{\circ}C$	30	W
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-65~150	$^{\circ}C$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	4.17	$^{\circ}C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^{\circ}C/W$

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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=30\text{mA}; I_B=0$	60		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.125\text{A}$		0.7	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=1\text{A}; V_{CE}=4\text{V}$		1.3	V
I_{CES}	Collector Cutoff Current	$V_{CE}=60\text{V}; V_{EB}=0$		0.2	mA
I_{CEO}	Collector Cutoff Current	$V_{CE}=30\text{V}; I_B=0$		0.3	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$		1.0	mA
h_{FE-1}	DC Current Gain	$I_C=0.2\text{A}; V_{CE}=4\text{V}$	40		
h_{FE-2}	DC Current Gain	$I_C=1\text{A}; V_{CE}=4\text{V}$	15	75	
f_T	Current-Gain—Bandwidth Product	$I_C=0.2\text{A}; V_{CE}=10\text{V}; f=1\text{MHz}$	3		MHz